

# S6200, S6210, S6220 SERIES

## SILICON CONTROLLED RECTIFIER

### FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
<b>Peak repetitive forward and reverse blocking voltage<sup>(1)</sup></b> S6200A, S6210A, S6220A S6200B, S6210B, S6220B S6200D, S6210D, S6220D S6200M, S6210M, S6220M	$V_{RRM}, V_{DRM}$	100 200 400 600	Volts
<b>Peak non-repetitive forward and non-repetitive reverse blocking voltage<sup>(1)</sup></b> S6200A, S6210A, S6220A S6200B, S6210B, S6220B S6200D, S6210D, S6220D S6200M, S6210M, S6220M	$V_{DSM}, V_{RSM}$	150 250 500 700	Volts
<b>Forward on-state current RMS</b> ( $T_C = 75^\circ\text{C}$ )	$I_{T(RMS)}$	20	Amps
<b>Peak non-repetitive surge current</b> (one cycle, 60Hz, preceded and followed by rated current, $T_C = 75^\circ\text{C}$ )	$I_{TSM}$	200	Amps
<b>Circuit fusing considerations</b> ( $T_J = -65$ to $+100^\circ\text{C}$ , $t = 8.3\text{ms}$ )	$I^2t$	170	$\text{A}^2\text{s}$
<b>Peak gate power</b> (10 $\mu\text{s}$ max.)	$P_{GM}$	40	Watts
<b>Average gate power</b>	$P_{G(AV)}$	0.5	Watts
<b>Operating junction temperature range</b>	$T_J$	-65 to +100	$^\circ\text{C}$
<b>Storage temperature range</b>	$T_{stg}$	-65 to +150	$^\circ\text{C}$
<b>Mounting torque</b>		30	In. lb.

Note 1: Ratings apply for open gate conditions. Thyristor devices shall not be tested with a constant current source for blocking capability such that the voltage applied exceeds the rated blocking voltage.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Maximum	Unit
<b>Thermal resistance, junction to case</b> S6200 SERIES S6210 SERIES, S6220 SERIES	$R_{\theta JC}$	1.2 1.4	$^\circ\text{C}/\text{W}$

**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

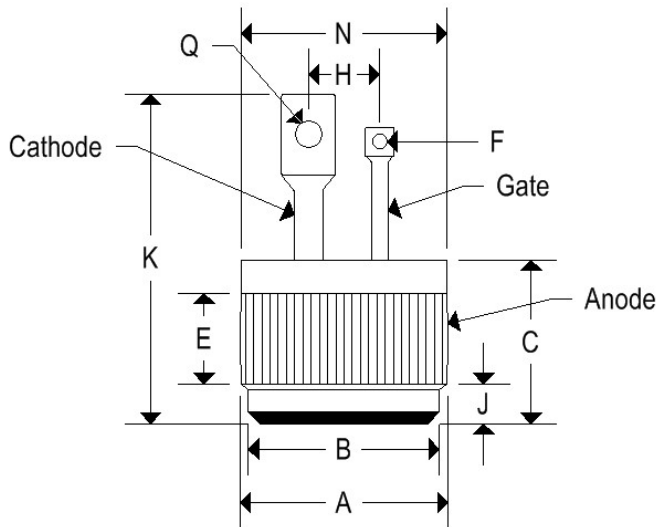
Characteristic	Symbol	Min.	Typ.	Max.	Unit
<b>Instantaneous forward breakover voltage</b> (gate open, $T_C = 100^\circ\text{C}$ ) S6200A, S6210A, S6220A S6200B, S6210B, S6220B S6200D, S6210D, S6220D S6200M, S6210M, S6220M	$V_{(BO)O}$	100 200 400 600	- - - -	- - - -	Volts
<b>Peak blocking current</b> (Rated $V_{DRM}$ @ $T_C = 100^\circ\text{C}$ ) $T_C = 25^\circ\text{C}$	$I_{RRM}$ $I_{DRM}$	- -	- -	10 2	$\mu\text{A}$ mA
<b>Peak on-state voltage</b> ( $I_T = 100\text{A}$ peak)	$V_T$	-	-	2.4	Volts
<b>Gate trigger current (continuous dc)</b> (Main terminal voltage = 12V, $R_L = 30\Omega$ )	$I_{GT}$	-	-	15	mA
<b>Gate trigger voltage (continuous dc)</b> (Main terminal voltage = 12V, $R_L = 30\Omega$ )	$V_{GT}$	-	-	2	Volts
<b>Holding current</b> (either direction) (Main terminal voltage = 12V, gate open)	$I_H$	-	-	20	mA
<b>Gate controlled turn-on time</b> ( $V_D = V_{(BO)O}$ , $I_T = 30\text{A}$ peak, $I_{GT} = 200\text{mA}$ , rise time = 0.1 $\mu\text{s}$ )	$t_{gt}$	-	2	-	$\mu\text{s}$
<b>Critical rate of rise of off-state voltage</b> ( $V_D = V_{(BO)O}$ , exponential rise, gate open, $T_C = 100^\circ\text{C}$ ) S6200A,D, S6210A,D, S6220A,D S6200B, S6210B, S6220B S6200D, S6210D, S6220D	dv/dt	10 10 10	100 150 75	- - -	V/ $\mu\text{s}$

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## MECHANICAL CHARACTERISTICS

<b>Case</b>	Digi PF1 (S6200 SERIES)
<b>Marking</b>	Body painted, alpha-numeric



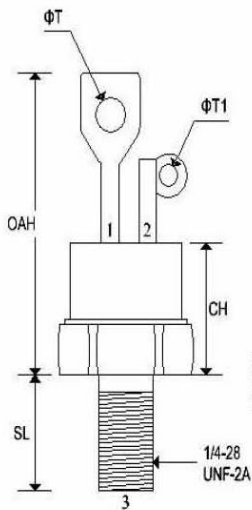
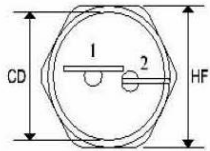
	DIGI PF1			
	Inches		Millimeters	
	Min	Max	Min	Max
<b>A</b>	0.501	0.505	12.730	12.830
<b>F</b>	-	0.160	-	4.060
<b>G</b>	0.085	0.095	2.160	2.410
<b>H</b>	0.060	0.070	1.520	1.780
<b>J</b>	0.300	0.350	7.620	8.890
<b>K</b>	-	1.050	-	26.670
<b>L</b>	-	0.670	-	17.020
<b>Q</b>	0.055	0.085	1.400	2.160

# S6200, S6210, S6220 SERIES

SILICON CONTROLLED RECTIFIER

**MECHANICAL CHARACTERISTICS**

<b>Case</b>	TO-48 (S6210 SERIES)
<b>Marking</b>	Body painted, alpha-numeric
<b>Polarity</b>	Cathode is stud



Pin 1: Cathode  
Pin 2: Gate  
Pin 3: Anode

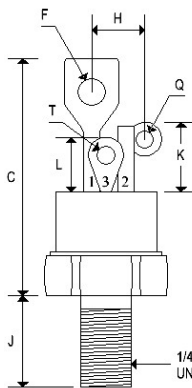
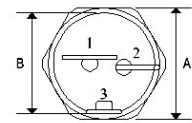
	TO-48			
	Inches		Millimeters	
	Min	Max	Min	Max
<b>CD</b>	-	0.543	-	13.793
<b>CH</b>	-	0.550	-	13.970
<b>HF</b>	0.544	0.563	13.817	14.301
<b>OAH</b>	-	1.193	-	30.303
<b>SL</b>	0.422	0.453	10.718	11.507
<b>ΦT</b>	0.125	0.165	3.175	4.191
<b>ΦT<sub>1</sub></b>	0.060	0.075	1.524	1.905

# S6200, S6210, S6220 SERIES

SILICON CONTROLLED RECTIFIER

## MECHANICAL CHARACTERISTICS

<b>Case</b>	TO-48 ISO (S6220 SERIES)
<b>Marking</b>	Body painted, alpha-numeric
<b>Polarity</b>	Cathode is stud



Pin 1: Cathode  
Pin 2: Gate  
Pin 3: Anode

1/4-28  
UNF-2A

	TO-48 ISO			
	Inches		Millimeters	
	Min	Max	Min	Max
<b>A</b>	0.551	0.559	14.000	14.200
<b>B</b>	0.501	0.505	12.730	12.830
<b>C</b>	-	1.280	-	32.510
<b>F</b>	-	0.160	-	4.060
<b>H</b>	-	0.265	-	6.730
<b>J</b>	0.420	0.455	10.670	11.560
<b>K</b>	0.300	0.350	7.620	8.890
<b>L</b>	0.255	0.275	6.480	6.990
<b>Q</b>	0.055	0.085	1.400	2.160
<b>T</b>	0.135	0.150	3.430	3.810